(19) JAPANESE PATENT OFFICE

PATENT ABSTRACTS OF JAPAN

(11) Publication number: **07093972 A**

(43) Date of publication of application: **07.04.95**

(51) Int. Cl **G11C 11/407**
G11C 11/409

(21) Application number: **05239297**

(22) Date of filing: **27.09.93**

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(54) **SEMICONDUCTOR MEMORY DEVICE**

(57) Abstract:

PURPOSE: To realize a high-speed semiconductor memory device which can generate the activation timing of a sense amplifier without being affected by an irregularity in a process.

CONSTITUTION: When one word line is activated, a voltage VDBL for a dummy bit line DBL which is held at a prescribed potential and a preset reference voltage VBS are compared by a differential-type comparator CMP. When the voltage VDBL becomes the reference voltage VBS or higher, an activation signal SACT is generated, the signal is input to a driver for a sense amplifier S/A, and the sense amplifier is activated.